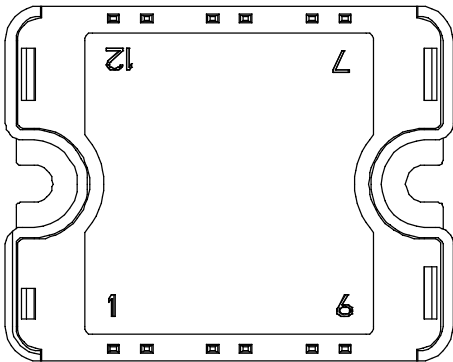
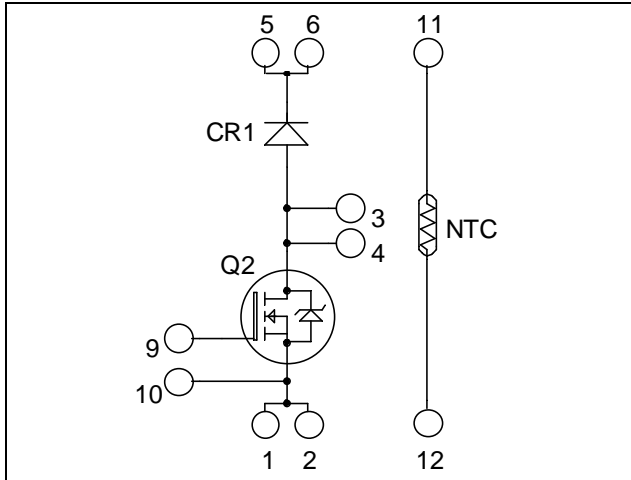


Boost chopper MOSFET Power Module

$V_{DSS} = 1200V$
 $R_{DSon} = 560m\Omega \text{ typ @ } T_j = 25^\circ C$
 $I_D = 18A \text{ @ } T_c = 25^\circ C$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features


- Power MOS 8TM MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1200	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	18
		$T_c = 80^\circ C$	13
I_{DM}	Pulsed Drain current	104	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	672	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	390
I_{AR}	Avalanche current (repetitive and non repetitive)	14	A


CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$			100	μA
			$T_j = 125^\circ\text{C}$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 14\text{A}$			560	672	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$		3	4	5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$				± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$			7736		pF
C_{oss}	Output Capacitance				715		
C_{rss}	Reverse Transfer Capacitance				92		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 600\text{V}$ $I_D = 14\text{A}$			300		nC
Q_{gs}	Gate – Source Charge				50		
Q_{gd}	Gate – Drain Charge				140		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C			50		ns
T_r	Rise Time	$V_{GS} = 15\text{V}$ $V_{Bus} = 800\text{V}$			31		
$T_{d(off)}$	Turn-off Delay Time	$I_D = 14\text{A}$			170		
T_f	Fall Time	$R_G = 2.2\Omega$			48		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$			100	μA
			$T_j = 125^\circ\text{C}$			500	
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$			30		A
V_F	Diode Forward Voltage	$I_F = 30\text{A}$			2.6	3.1	V
		$I_F = 60\text{A}$			3.2		
		$I_F = 30\text{A}$	$T_j = 125^\circ\text{C}$		1.8		
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		300		ns
			$T_j = 125^\circ\text{C}$		380		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		360		nC
			$T_j = 125^\circ\text{C}$		1700		

Thermal and package characteristics

Symbol	Characteristic		Min	Typ	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance		Transistor			0.32	$^\circ\text{C}/\text{W}$
			Diode			1.2	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}, I_{isol} < 1\text{mA}, 50/60\text{Hz}$		2500			V	
T_j	Operating junction temperature range		-40		150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range		-40		125		
T_C	Operating Case Temperature		-40		100		
Torque	Mounting torque	To heatsink M4	2.5		4.7	N.m	
Wt	Package Weight				80	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

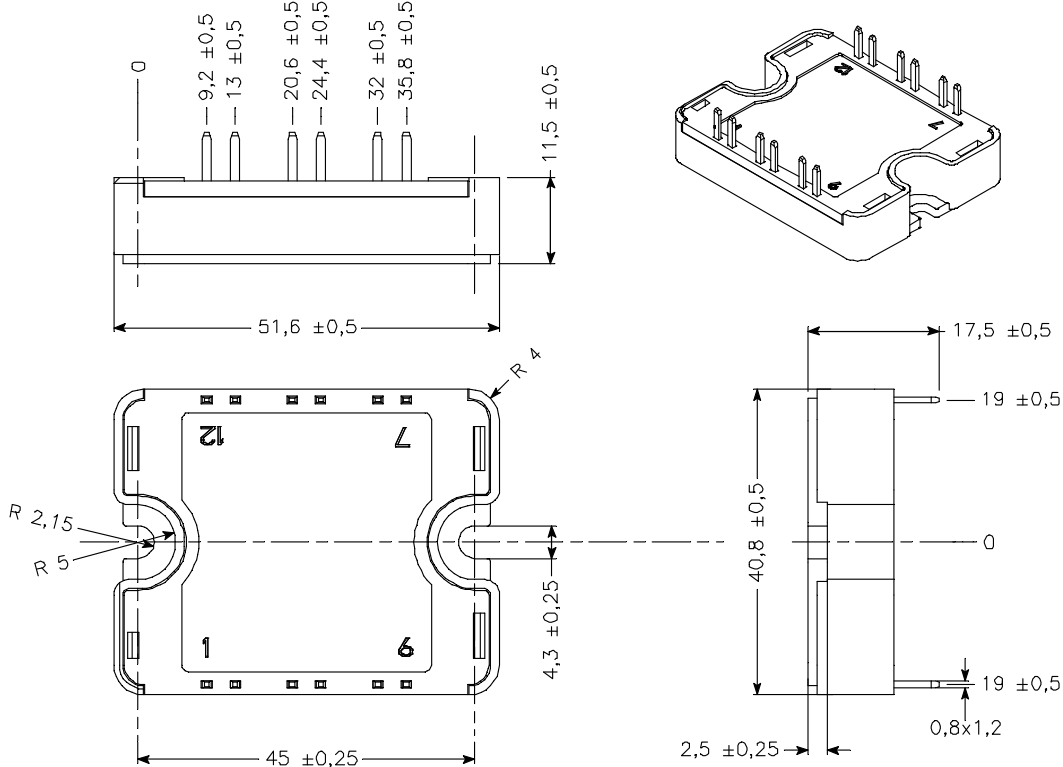
Symbol Characteristic

		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

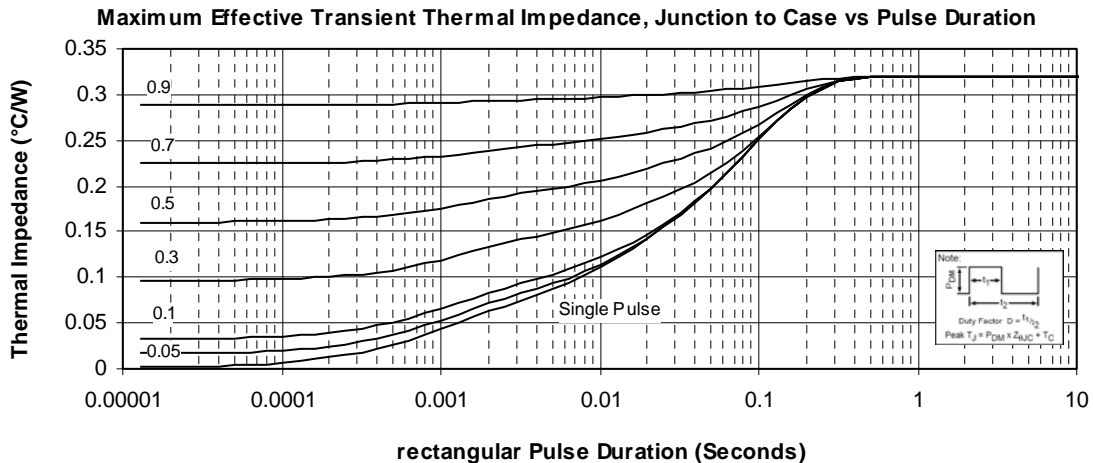
T: Thermistor temperature
 R_T: Thermistor value at T

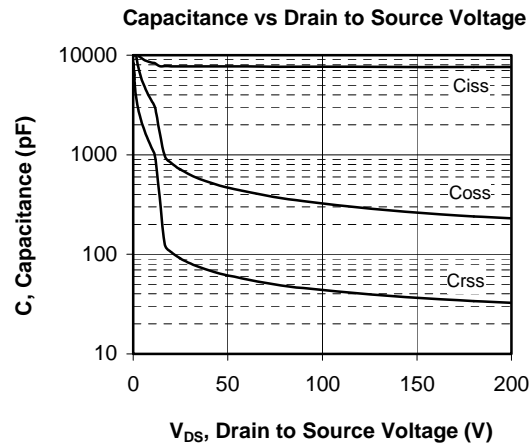
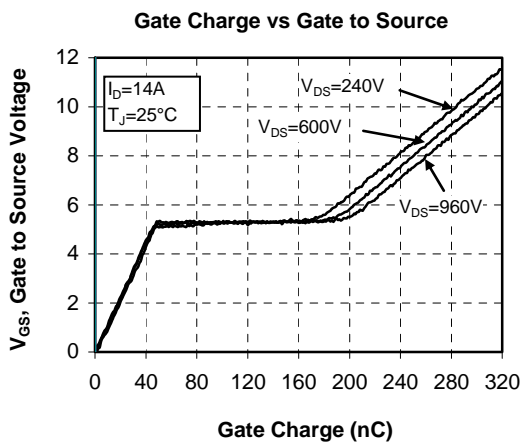
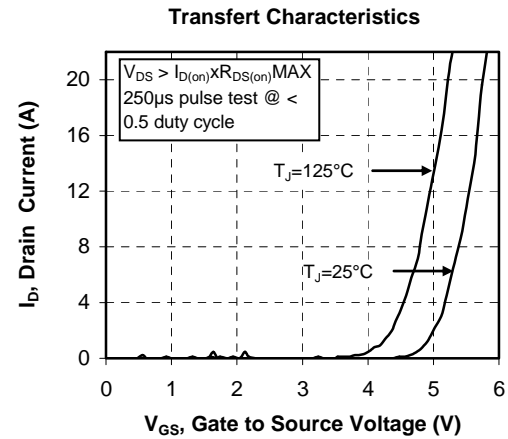
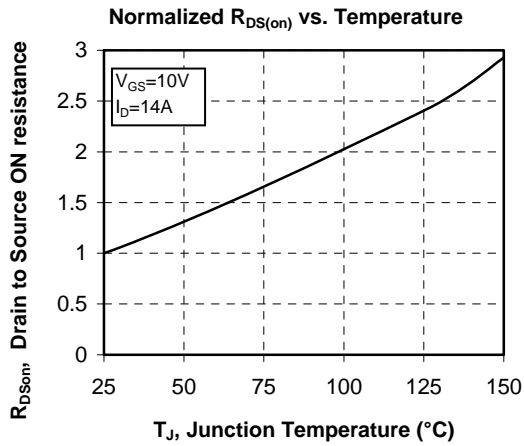
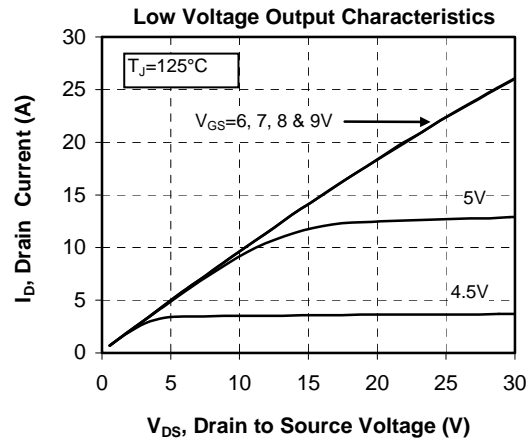
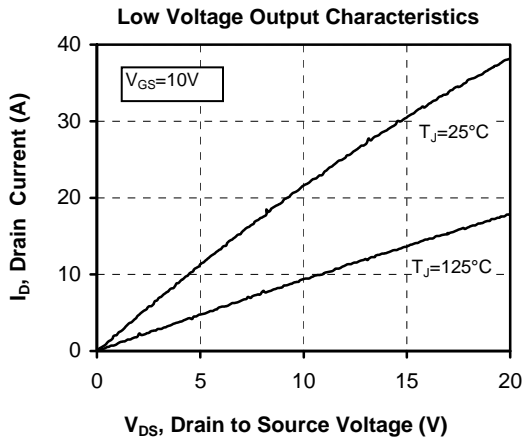
SP1 Package outline (dimensions in mm)



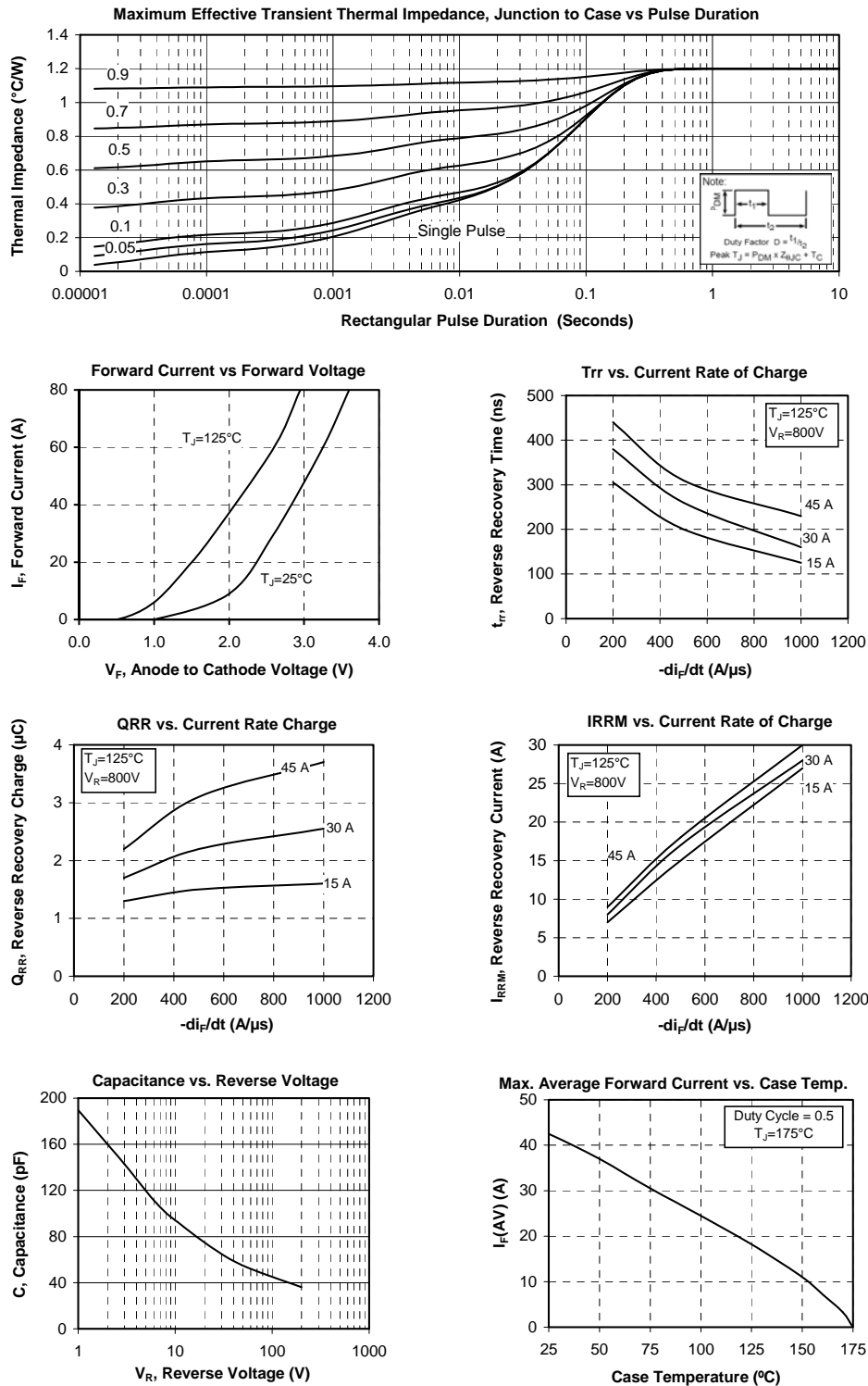
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Typical Mosfet Performance Curve





Typical Diode Performance Curve



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.